

FEATURES

Complementary Type The NPN Transistor
MMBT3904 is Recommended
Epitaxial Planar Die Construction



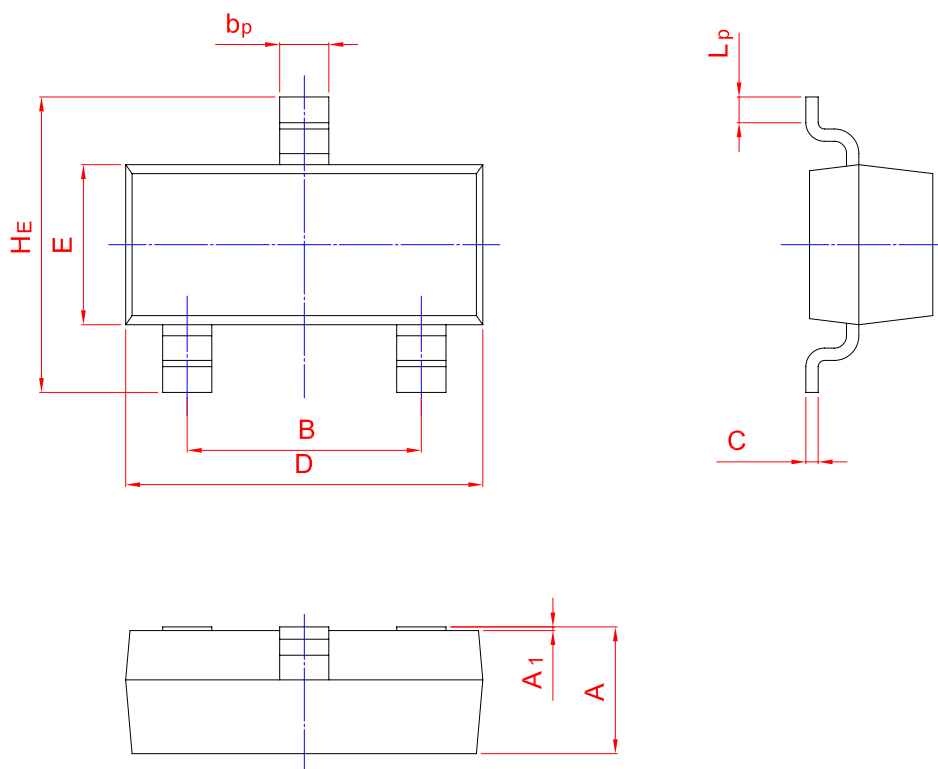
MARKING: 2A

MAXIMUM RATINGS ($T_a=25$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-200	mA
P_C	Total Device Dissipation	200	mW
R_{JA}	Thermal Resistance Junction to Ambient	625	/W
T_J	Junction Temperature	150	
T_{stg}	Storage Temperature	-55 ~ +150	

ELECTRICAL CHARACTERISTICS ($T_a=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-40		V



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.75	0.35	0.08	2.70	1.20	2.20	0.013	0.20